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REV. 2

#### STANDARD

## **Table 1: Main Features**

Symbol	Value	Unit
I <sub>T(RMS)</sub>	6	А
V <sub>DRM</sub> /V <sub>RRM</sub>	600 and 1000	V
I <sub>GT</sub>	15	mA

## DESCRIPTION

February 2006

The TYN606 and TYN1006 family of Silicon Controlled Rectifiers are high performance glass passivated technology.

This general purpose Family of Silicon Controlled

Symbol	Parameter			Value	Unit
I <sub>T(RMS)</sub>	RMS on-state current (180° conduction angle) $T_c = 110^{\circ}C$		6	А	
IT <sub>(AV)</sub>	Average on-state current (180° conduc	tion angle)	T <sub>c</sub> = 110°C	3.8	А
l=a	Non repetitive surge peak on-state	t <sub>p</sub> = 8.3 ms	T <sub>i</sub> = 25°C	73	А
I <sub>TSM</sub>	current	t <sub>p</sub> = 10 ms	$\frac{1}{j} = 250$	70	
l²t	I <sup>²</sup> t Value for fusing	t <sub>p</sub> = 10 ms	T <sub>j</sub> = 25°C	24.5	A <sup>2</sup> s
dl/dt	$\label{eq:transformation} \begin{array}{l} Critical \mbox{ rate of rise of on-state current} \\ I_G = 100 \mbox{ mA }, \mbox{ dI}_G/\mbox{ dt} = 0.1 \mbox{ A/}\mbox{ \mus} \end{array} \qquad T_j = 12 \label{eq:transformation}$		T <sub>j</sub> = 125°C	50	A/µs
I <sub>GM</sub>	Peak gate current $t_p = 20 \ \mu s$		T <sub>j</sub> = 125°C	4	А
$P_{G(AV)}$	Average gate power dissipation		T <sub>j</sub> = 125°C	1	W
$P_{GM}$	Maximum gate power $t_p = 20 \ \mu s$ $T_j = T_j = 0 \ \mu s$		T <sub>j</sub> = 125°C	10	W
$V_{DRM}$	Repetitive peak off-state voltageTYN606TYN1006 $T_j = 125^{\circ}C$		T: = 125°C	600	V
V <sub>RRM</sub>			1] = 120 0	1000	v
T <sub>stg</sub> T <sub>j</sub>	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C
ΤL	Maximum lead temperature for soldering during 10s at 2mm from case 260			260	°C

Rectifiers is designed for power supply up to 400Hz on resistive or inductive load.

Table 3: Absolute Ratings (limiting values)

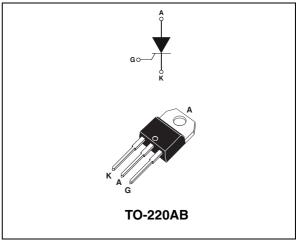
# **TO-220AB**

## **Table 2: Order Codes**

Part N	umbers	Marking
TYN	606RG	TYN606
TYN1	006RG	TYN1006

## **TYN606 TYN1006**

6A SCRs





## **TYN606 / TYN1006**

Symbol	Test Conditions		Value	Unit	
I <sub>GT</sub>	$V_{\rm D} = 12  \text{V}  (\text{D.C.})  \text{R}_1 = 33  \Omega$		MAX.	15	mA
$V_{GT}$	$v_{\rm D} = 12 v (D.0.) + 11 = 33.22$		MAX.	1.5	V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$	T <sub>j</sub> = 110°C	MIN.	0.2	V
t <sub>gt</sub>	$V_D = V_{DRM}$ $I_G = 40$ mA $dI_G/dt = 0.5$ A/µs		TYP.	2	μs
Ι <sub>Η</sub>	I <sub>T</sub> = 100 mA Gate open		MAX.	30	mA
١L	$I_{G} = 1.2 \times I_{GT}$		TYP.	50	mA
dV/dt	$ \begin{array}{l} \mbox{Linear slope up to:} \\ \mbox{V}_D = \ 67 \ \% \ \mbox{V}_{DRM} \ \ \mbox{Gate open} \end{array} \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $		MIN.	200	V/µs
$V_{TM}$	I <sub>TM</sub> = 12 A tp = 380 μs		MAX.	1.6	V
I <sub>DRM</sub>	V <sub>DBM</sub> = V <sub>BBM</sub>	$T_j = 25^{\circ}C$	MAX.	10	μA
I <sub>RRM</sub>		T <sub>j</sub> = 110°C		2	mA
t <sub>q</sub>		$T_j = 110^{\circ}C$	TYP.	70	μs

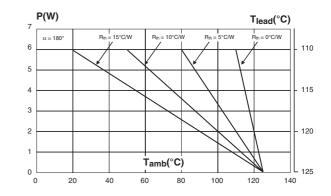
#### Tables 4: Electrical Characteristics (T<sub>i</sub> = 25°C, unless otherwise specified)

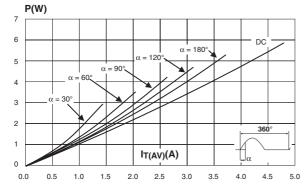
## **Table 5: Thermal Resistance**

Symbol	Parameter		Unit
R <sub>th(j-c)</sub>	Junction to case (D.C.)	2.5	°C/W
R <sub>th(j-a)</sub>	Junction to ambient	60	°C/W

## Figure 1: Maximum average power dissipation versus average on-state current

# Figure 2: Correlation between maximum average power dissipation and maximum allowable temperature ( $T_{amb}$ and $T_{lead}$ )

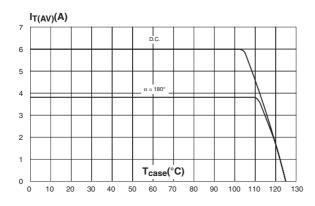






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## Figure 3: Average on-state current versus case temperature



## Figure 5: Relative variation of gate trigger current versus junction temperature

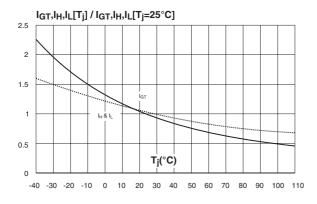


Figure 7: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10 ms, and corresponding values of  $l^2t$ 

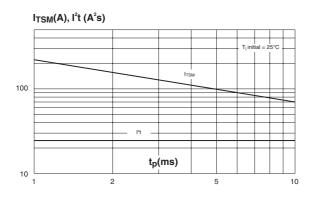


Figure 4: Relative variation of thermal impedance versus pulse duration

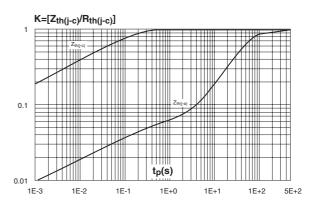
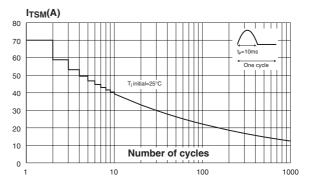
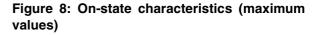
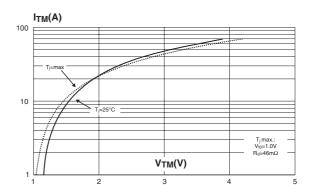


Figure 6: Surge peak on-state current versus number of cycles









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## TYN606 / TYN1006

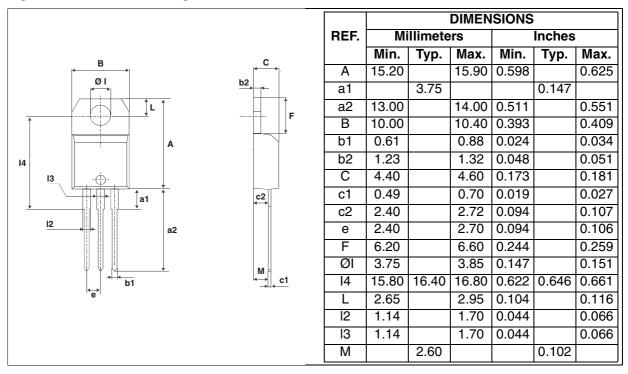
#### **Figure 9: Ordering Information Scheme**

TYN 6 06 RG
Standard SCR series
Voltage 6 = 600V 10 = 100V
<u>Current</u> 06 = 6A
Packing mode   RG = Tube

#### **Table 6: Product Selector**

Part Numbers	s Voltage (xx) Sensitivity		Package	
Fait Numbers	600 V	1000 V		
TYN606RG	Х		15 mA	TO-220AB
TYN1006RG		Х	15 mA	TO-220AB

#### Figure 10: TO-220AB Package Mechanical Data



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: <u>www.st.com</u>.

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## **Table 7: Ordering Information**

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
TYN606RG	TYN606	TO-220AB	2.3 g	50	Tube
TYN1006RG	TYN1006		2.0 g	50	Tabe

## **Table 8: Revision History**

Date	Revision	Description of Changes
Sep-2001	1A	First issue.
13-Feb-2006	2	TO-220AB delivery mode changed from bulk to tube. ECOPACK statement added.



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